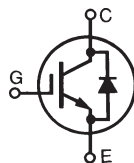


1200V XPT™ IGBT GenX3™ w/ Diode

IXYJ20N120C3D1

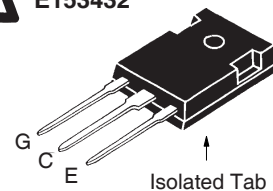
(Electrically Isolated Tab)

High-Speed IGBT
for 20-50 kHz Switching



$V_{CES} = 1200V$
 $I_{C110} = 9A$
 $V_{CE(sat)} \leq 3.4V$
 $t_{fi(typ)} = 108ns$

ISO TO-247™
 E153432



G = Gate C = Collector
 E = Emitter

Symbol	Test Conditions	Maximum Ratings	
		Value	Unit
V_{CES}	$T_J = 25^\circ C$ to $150^\circ C$	1200	V
V_{CGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GE} = 1M\Omega$	1200	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ C$	21	A
I_{C110}	$T_C = 110^\circ C$	9	A
I_{F110}	$T_C = 110^\circ C$	15	A
I_{CM}	$T_C = 25^\circ C$, 1ms	84	A
I_A	$T_C = 25^\circ C$	10	A
E_{AS}	$T_C = 25^\circ C$	400	mJ
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 150^\circ C$, $R_G = 10\Omega$ Clamped Inductive Load	$I_{CM} = 40$ @ $V_{CE} \leq V_{CES}$	A
P_C	$T_C = 25^\circ C$	105	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ C$
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	$^\circ C$
M_d	Mounting Torque	1.13/10	Nm/lb.in.
V_{ISOL}	50/60 Hz, RM, t = 1min	2500	V~
Weight		5	g

Features

- Optimized for Low Switching Losses
- Silicon Chip on Direct-Copper Bond (DCB) Substrate
- Isolated Mounting Surface
- 2500V~ Electrical Isolation
- Square RBSOA
- Positive Thermal Coefficient of $V_{ce(sat)}$
- Anti-Parallel Ultra Fast Diode
- Avalanche Rated

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- High Frequency Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu A$, $V_{GE} = 0V$	1200		V
$V_{GE(th)}$	$I_C = 250\mu A$, $V_{CE} = V_{GE}$	3.0		V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ $T_J = 125^\circ C$			25 μA 350 μA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 20A$, $V_{GE} = 15V$, Note 1 $T_J = 150^\circ C$		4.0	3.4 V V

Symbol Test Conditions		Characteristic Values		
(T _J = 25°C Unless Otherwise Specified)		Min.	Typ.	Max.
g_{fs}	I _C = 20A, V _{CE} = 10V, Note 1	7.0	11.5	S
C_{ies}	V _{CE} = 25V, V _{GE} = 0V, f = 1MHz		1110	pF
C_{oes}			120	pF
C_{res}			27	pF
Q_{g(on)}	I _C = 20A, V _{GE} = 15V, V _{CE} = 0.5 • V _{CES}		53	nC
Q_{ge}			9	nC
Q_{gc}			22	nC
t_{d(on)}	Inductive load, T_J = 25°C I _C = 20A, V _{GE} = 15V V _{CE} = 0.5 • V _{CES} , R _G = 10Ω Note 2		20	ns
t_{ri}			29	ns
E_{on}			1.3	mJ
t_{d(off)}			90	ns
t_{fi}			108	ns
E_{off}			0.5	1.0
t_{d(on)}	Inductive load, T_J = 150°C I _C = 20A, V _{GE} = 15V V _{CE} = 0.5 • V _{CES} , R _G = 10Ω Note 2		20	ns
t_{ri}			40	ns
E_{on}			3.7	mJ
t_{d(off)}			115	ns
t_{fi}			105	ns
E_{off}			0.7	mJ
R_{thJC}				1.19 °C/W
R_{thCS}		0.15		°C/W

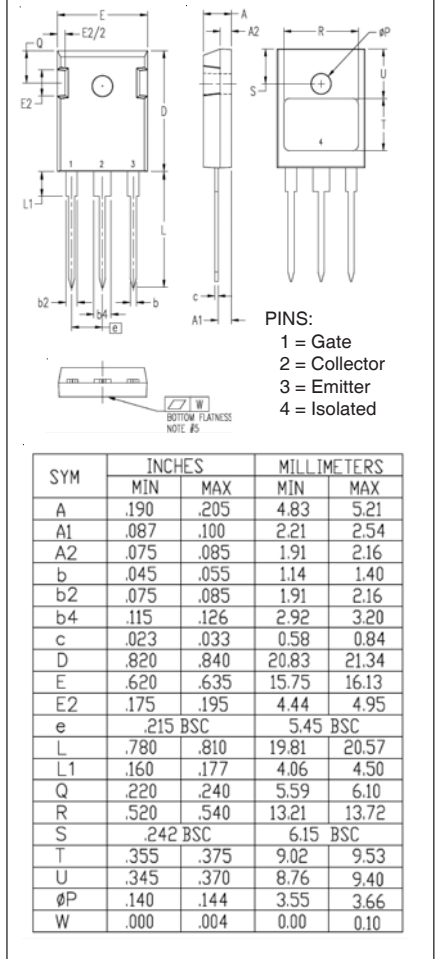
Reverse Diode (FRED)

Symbol Test Conditions		Characteristic Value		
(T _J = 25°C, Unless Otherwise Specified)		Min.	Typ.	Max.
V_F	I _F = 30A, V _{GE} = 0V, Note 1			3.00 V
		T _J = 150°C	1.75	V
I_{RM}	I _F = 30A, V _{GE} = 0V, -di _F /dt = 100A/μs, V _R = 600V	T _J = 100°C		9 A
t_{rr}			195	ns
R_{thJC}				1.25 °C/W

Notes:

1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.
2. Switching times & energy losses may increase for higher V_{CE}(clamp), T_J or R_G.

ISO TO-247 (IXYJ) OUTLINE



IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

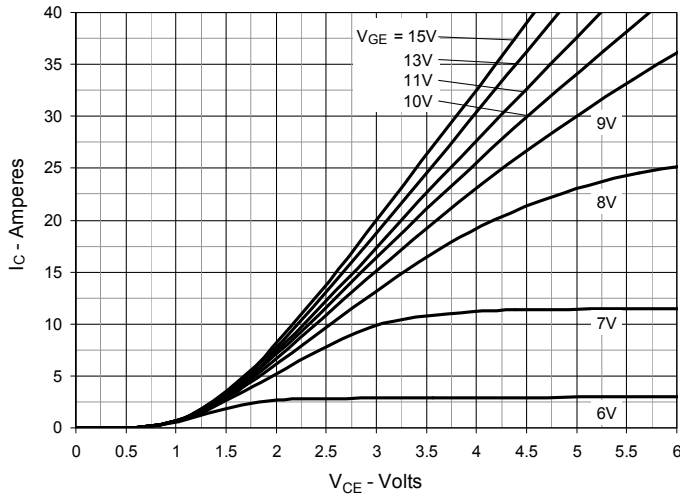
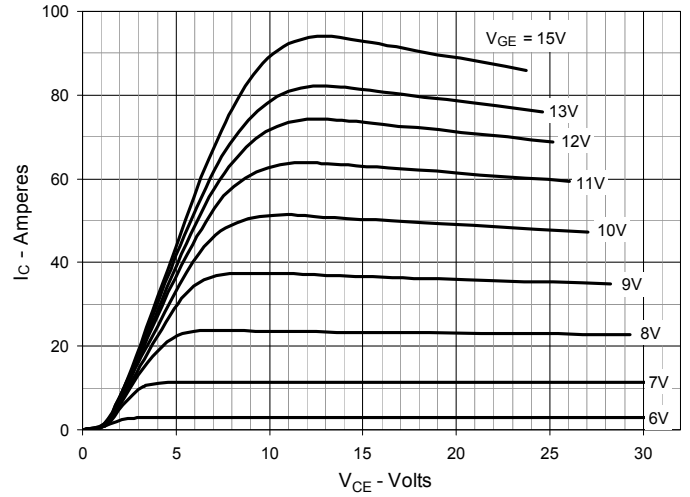
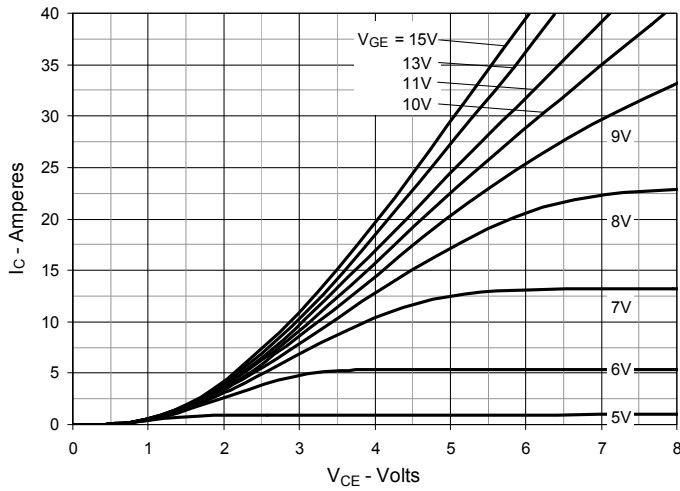
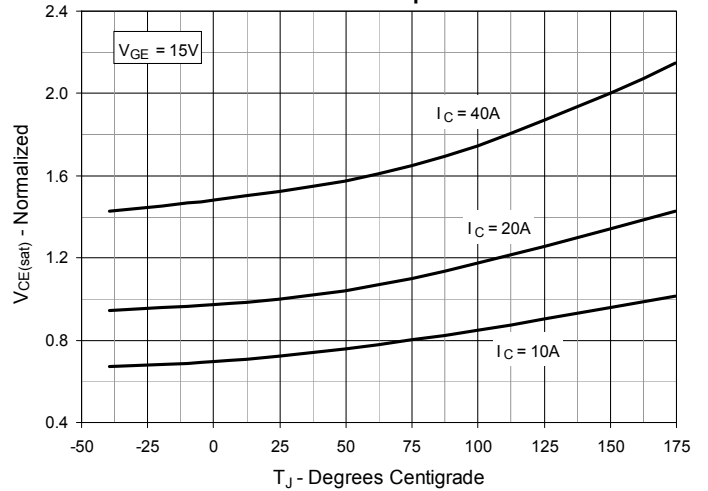
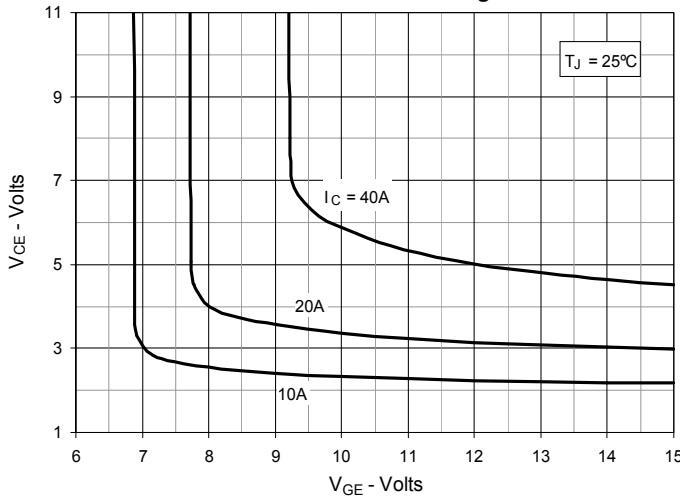
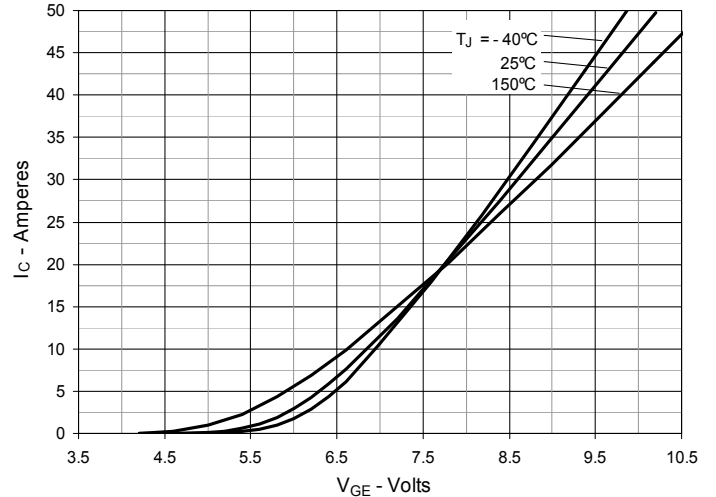
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 3. Output Characteristics @ $T_J = 150^\circ\text{C}$

Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

Fig. 6. Input Admittance


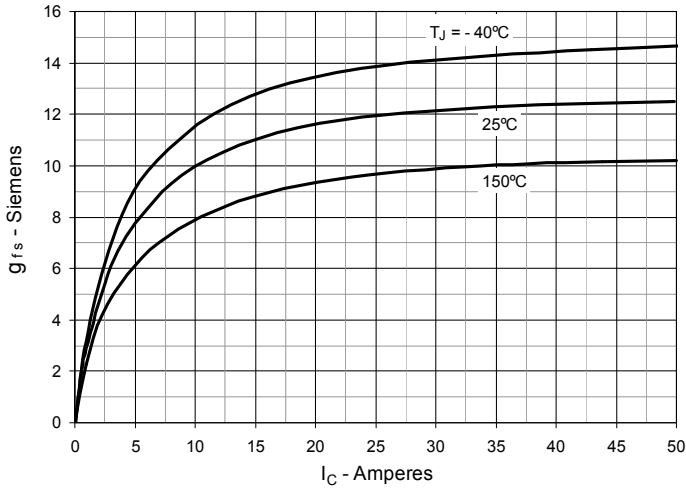
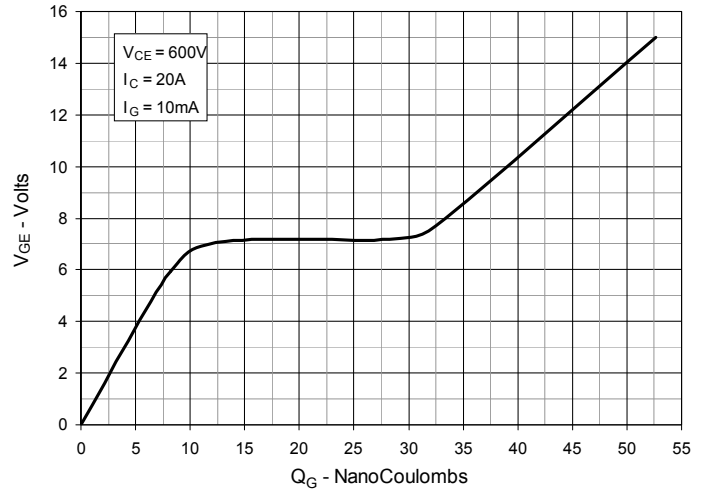
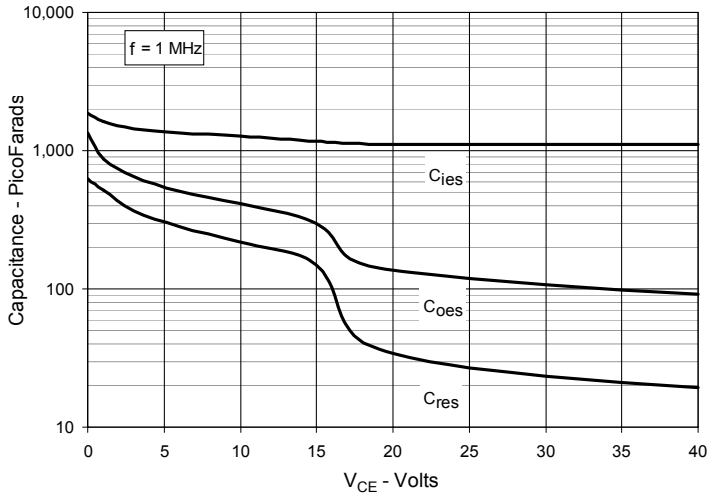
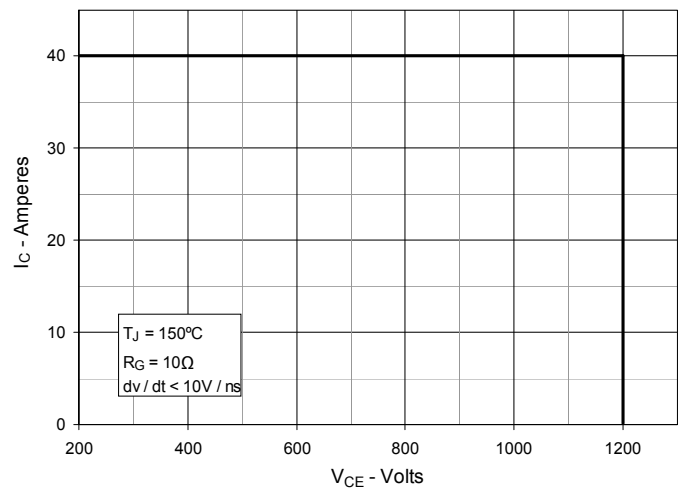
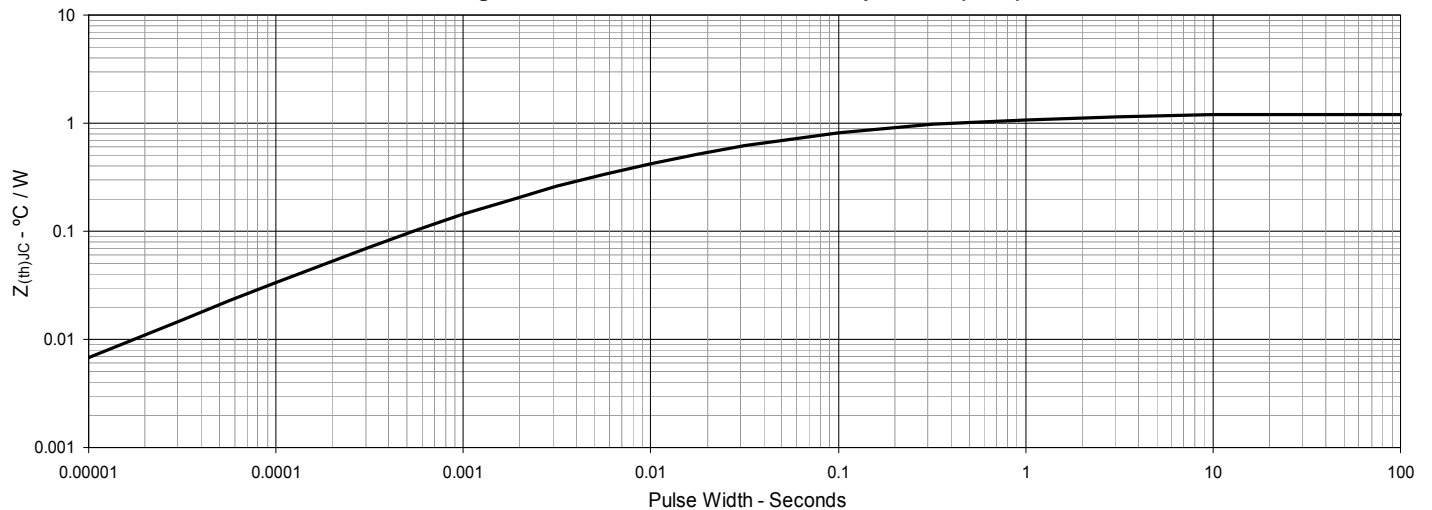
Fig. 7. Transconductance

Fig. 8. Gate Charge

Fig. 9. Capacitance

Fig. 10. Reverse-Bias Safe Operating Area

Fig. 11. Maximum Transient Thermal Impedance (IGBT)


Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance

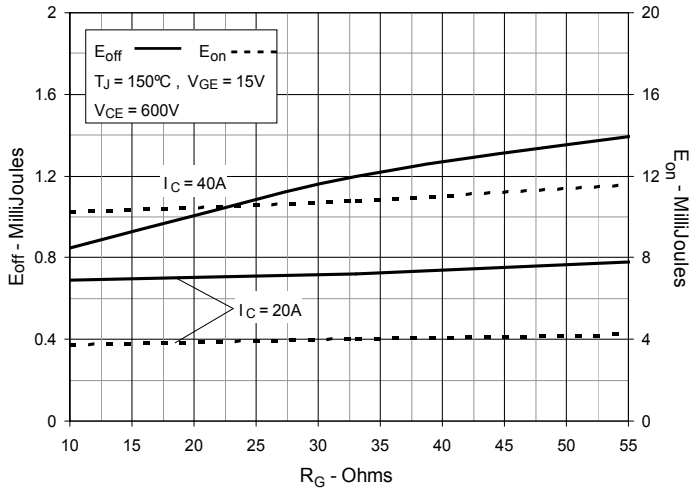


Fig. 13. Inductive Switching Energy Loss vs. Collector Current

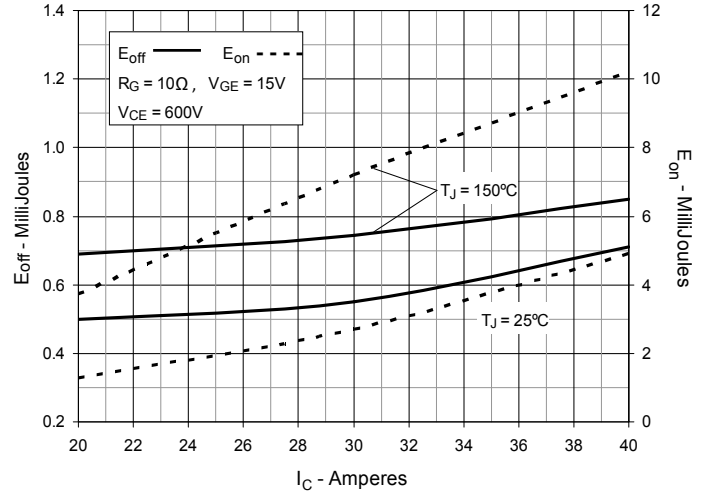


Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature

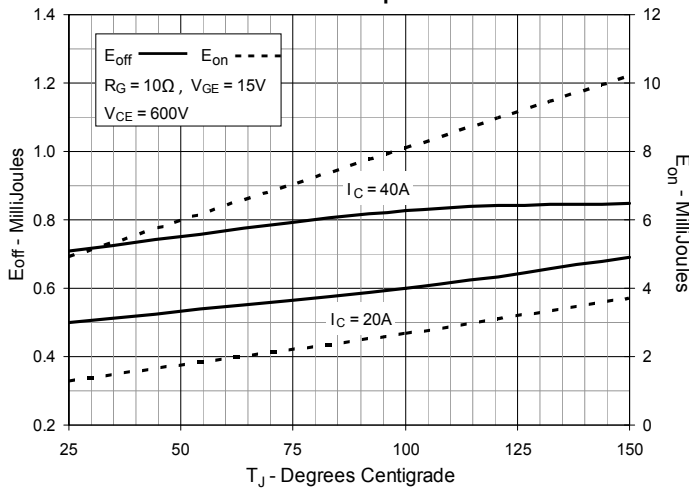


Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance

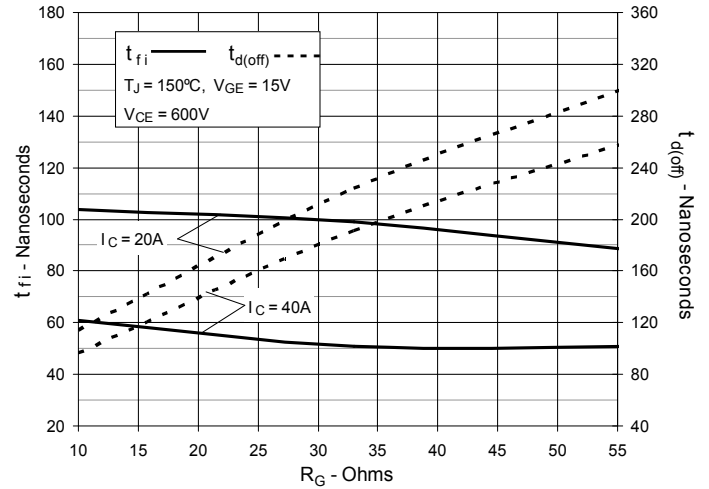


Fig. 16. Inductive Turn-off Switching Times vs. Collector Current

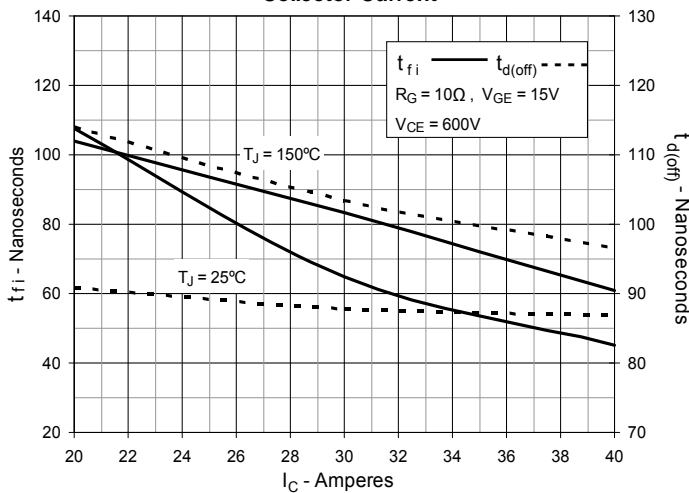


Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature

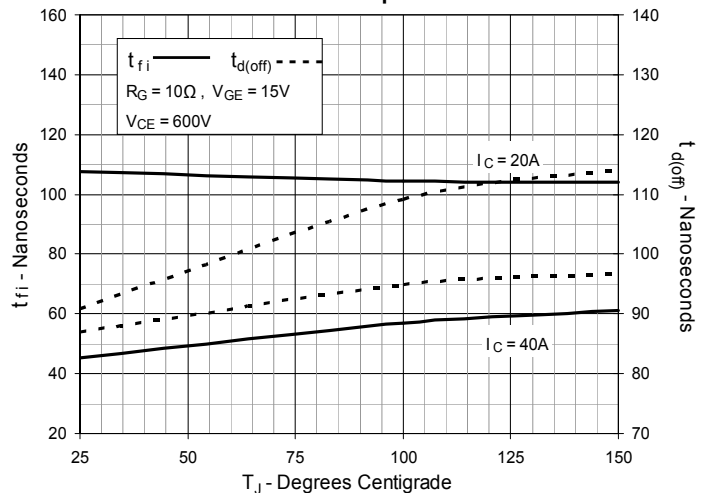


Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance

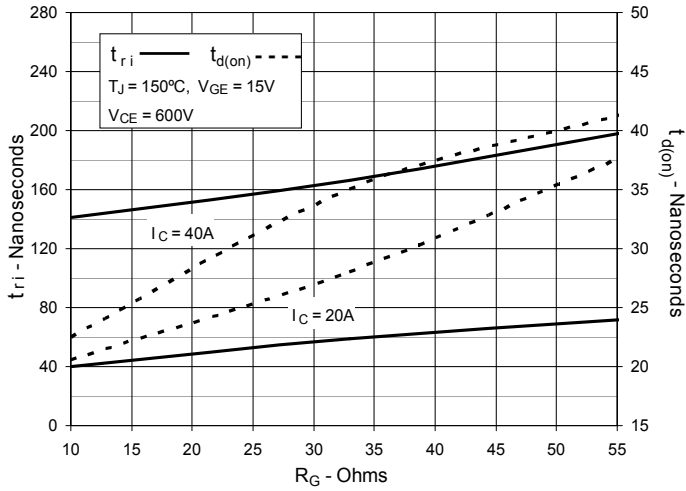


Fig. 19. Inductive Turn-on Switching Times vs. Collector Current

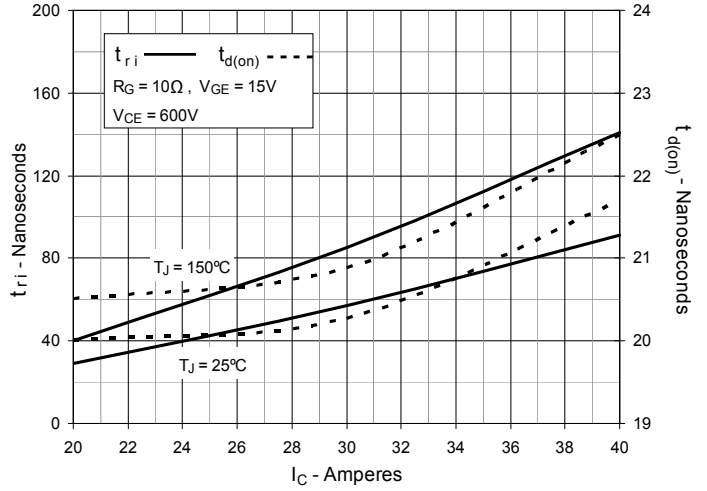


Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature

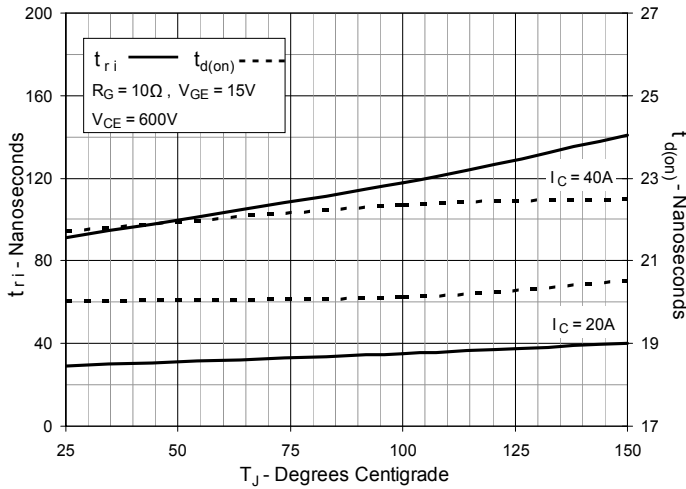


Fig. 21. Maximum Peak Load Current vs. Frequency

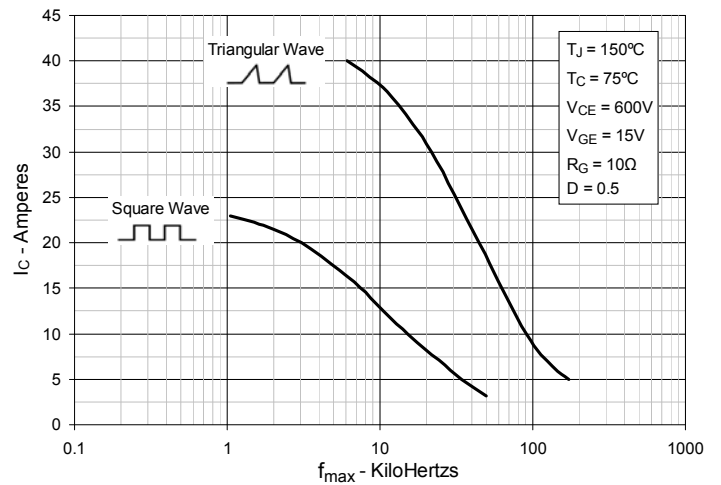


Fig. 22. Maximum Transient Thermal Impedance (Diode)

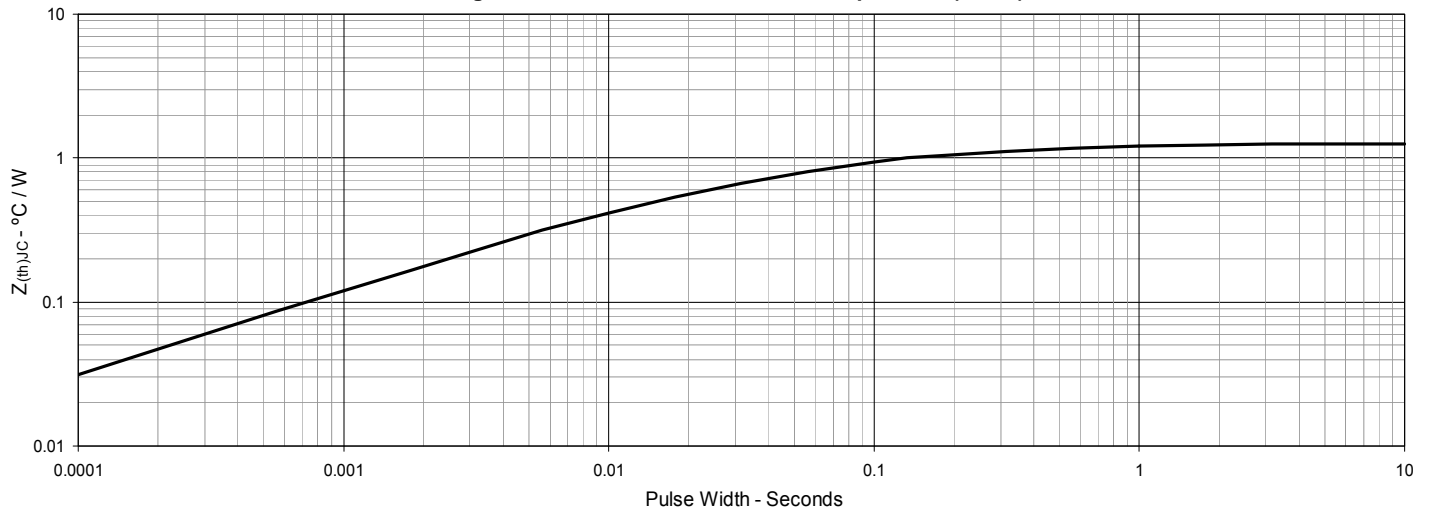
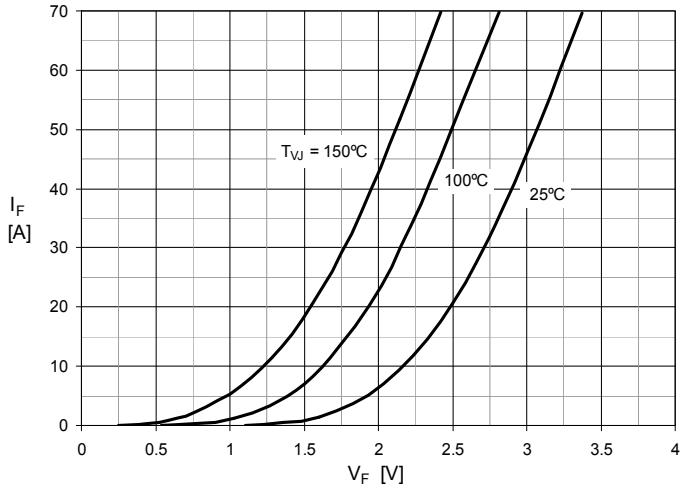
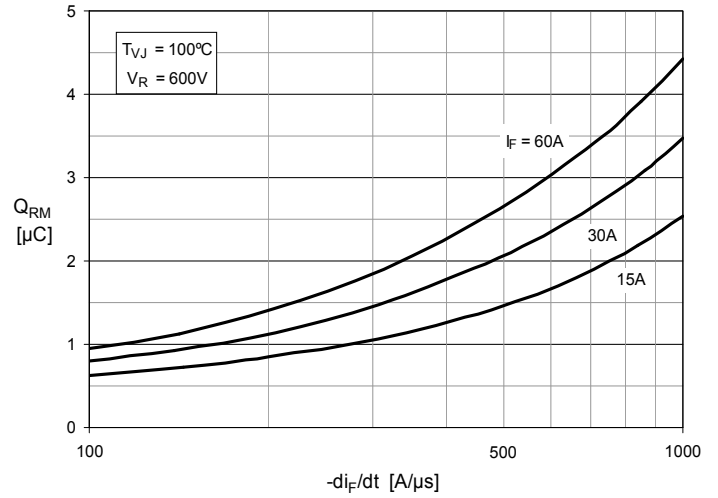
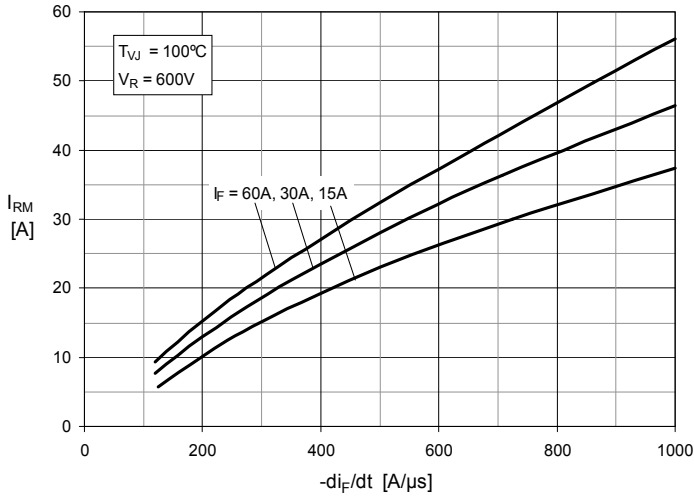
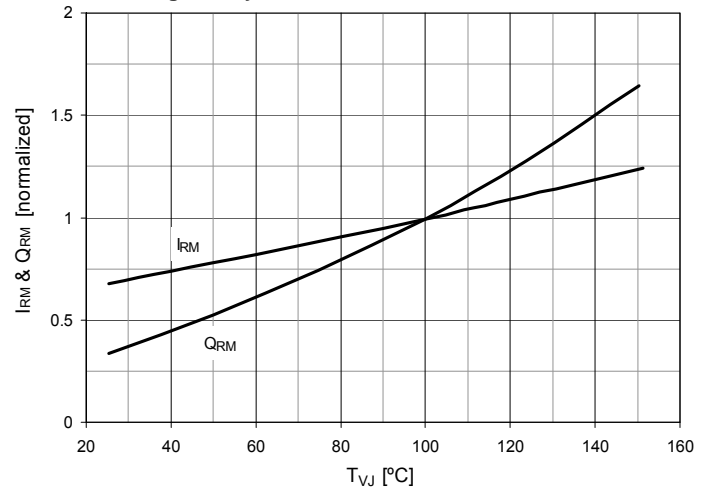
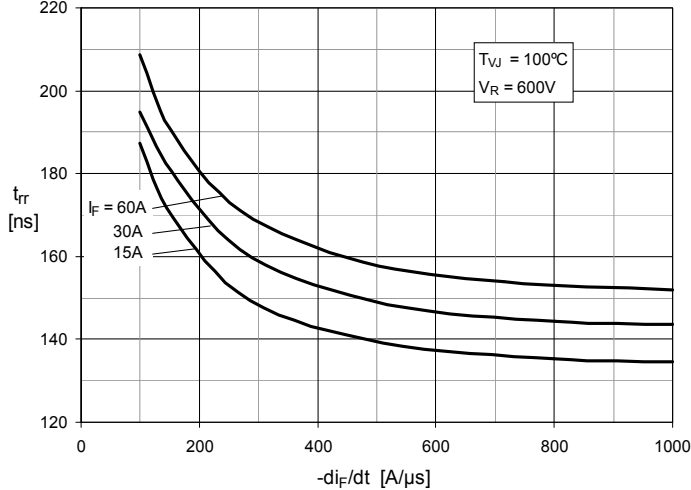


Fig. 23. Forward Current I_F vs V_F

Fig. 24. Reverse Recovery Charge Q_{RM} vs. $-di_F/dt$

Fig. 25. Peak Reverse Current I_{RM} vs. $-di_F/dt$

Fig. 26. Dynamic Parameters Q_{RM} , I_{RM} vs. T_{VJ}

Fig. 27. Recovery Time t_{rr} vs. $-di_F/dt$

Fig. 28. Peak Forward Voltage V_{FR} , t_{rr} vs $-di_F/dt$
